

**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = 25°C
100V	3.0Ω @ V <sub>GS</sub> = 10V	0.6A
	4.5Ω @ V <sub>GS</sub> = 5.0V	0.5A

**Description**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

**Applications**

- DC-DC Converters
- Power Management Functions

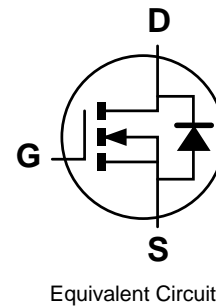
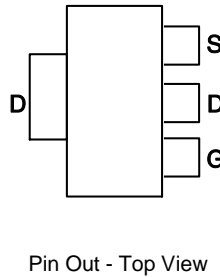
**Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

**Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.112 grams (Approximate)

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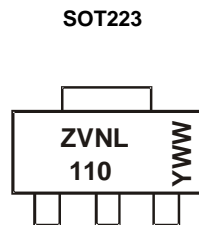


**Ordering Information** (Note 4)

Part Number	Compliance	Case	Packaging
ZVNL110GTA	Standard	SOT223	1,000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



ZVNL110 = Product Type Marking Code  
 YWW = Date Code Marking  
 Y or Ȳ = Last Digit of Year (ex: 5= 2015)  
 WW or WW̄ = Week Code (01-53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	100	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	0.6	A
		T <sub>A</sub> = +70°C		0.5	
Pulsed Drain Current (10µs Pulse, Duty Cycle ≤ 1%)			I <sub>DM</sub>	6	A
Maximum Body Diode Continuous Current (Note 6)			I <sub>S</sub>	1.5	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P <sub>D</sub>	1.1	W
	(Note 6)		2.0	
Thermal Resistance, Junction to Ambient	(Note 5)	R <sub>θJA</sub>	113	°C/W
	(Note 6)		61	
Thermal Resistance, Junction to Case	(Note 6)	R <sub>θJC</sub>	6.6	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	10 100	µA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +125°C
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
On-State Drain Current	I <sub>D(ON)</sub>	750	—	—	mA	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 5V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.75	—	1.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	3.0	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 500mA
		—	—	4.5		V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 250mA
Forward Transconductance	g <sub>fs</sub>	225	—	—	mS	V <sub>DS</sub> = 25V, I <sub>D</sub> = 500mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	47	75	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	23	25		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	6	8		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	2	7	ns	V <sub>DD</sub> = 25V, V <sub>GS</sub> = 10V, R <sub>G</sub> = 6.0Ω, I <sub>D</sub> = 1.0A
Turn-On Rise Time	t <sub>r</sub>	—	3	12		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	5	15		
Turn-Off Fall Time	t <sub>f</sub>	—	2	13		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

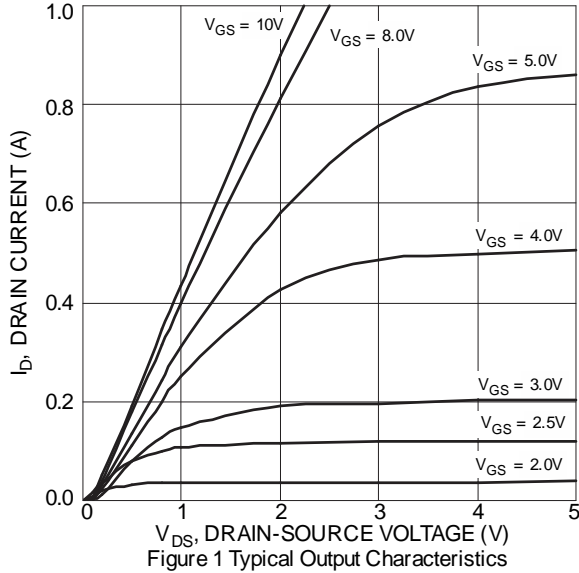


Figure 1 Typical Output Characteristics

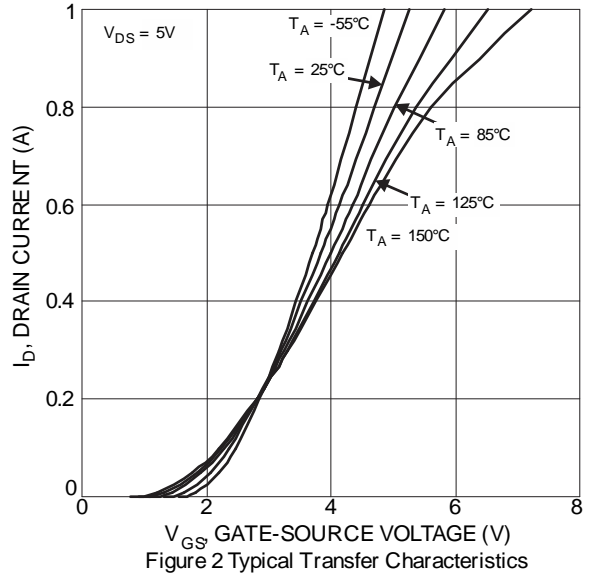


Figure 2 Typical Transfer Characteristics

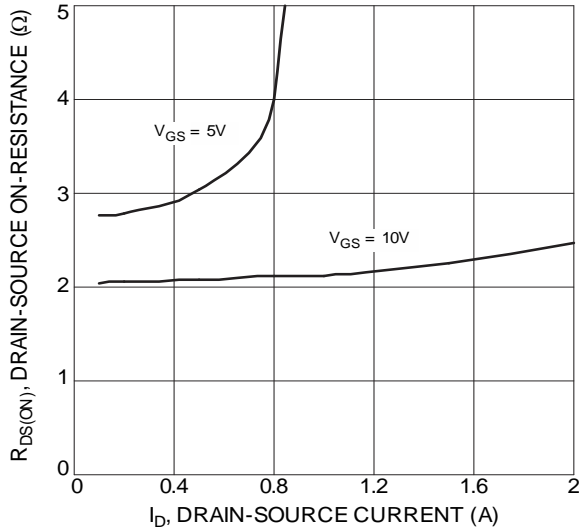


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

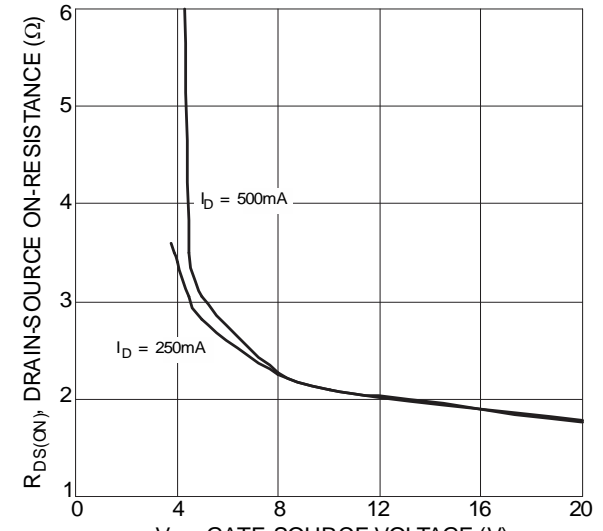


Figure 4 Typical Transfer Characteristics

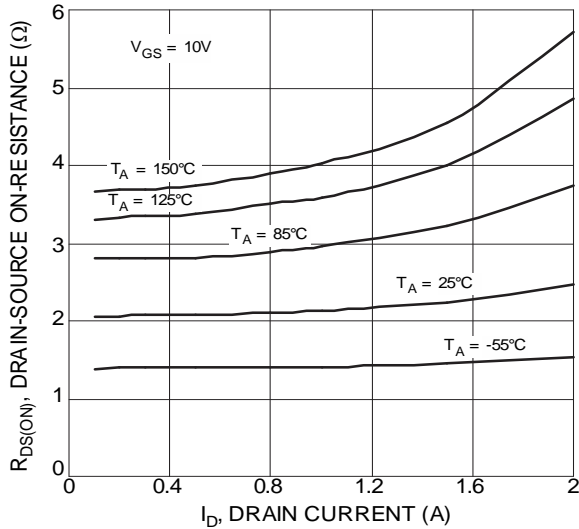


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

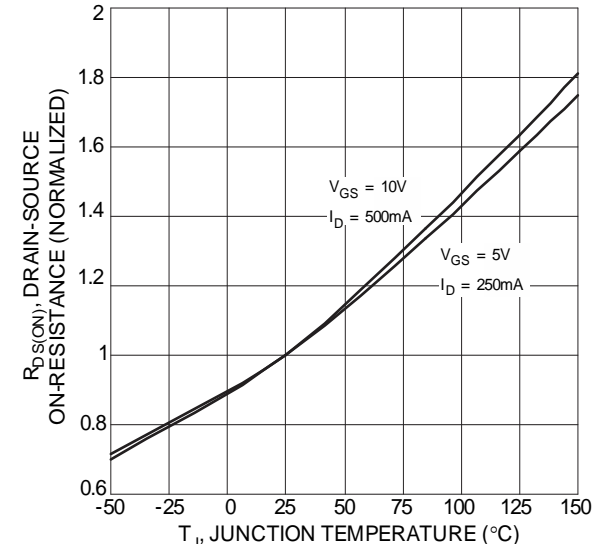


Figure 6 On-Resistance Variation with Temperature

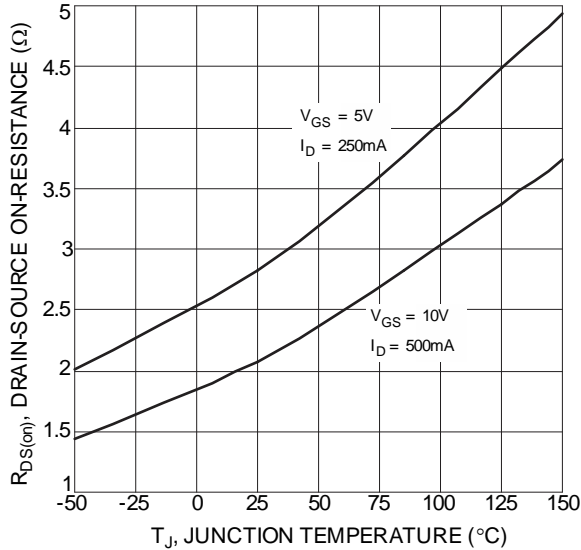


Figure 7 On-Resistance Variation with Temperature

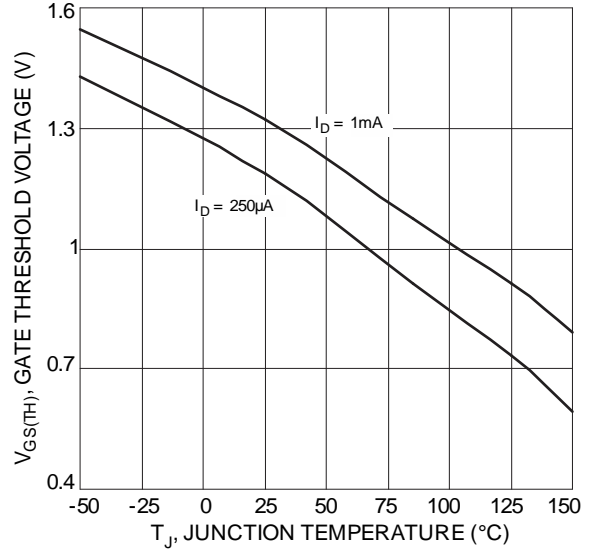


Figure 8 Gate Threshold Variation vs. Temperature

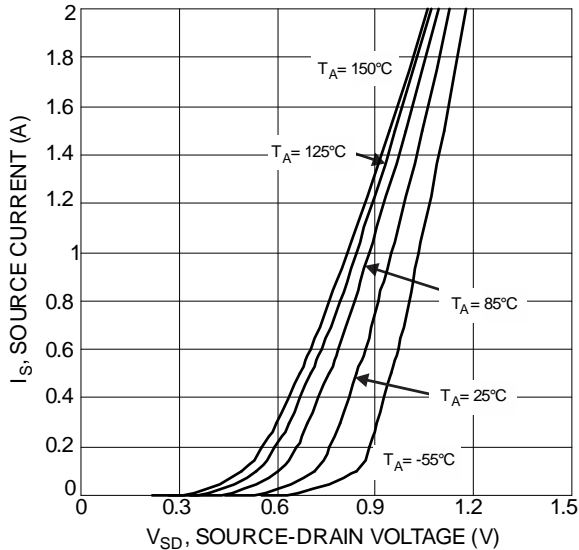


Figure 9 Diode Forward Voltage vs. Current

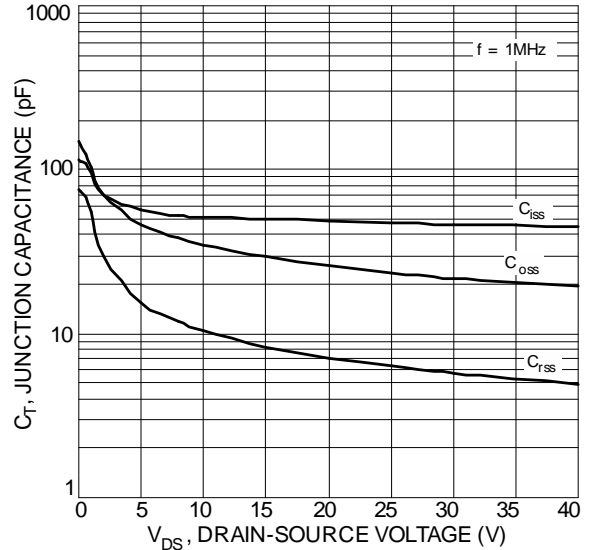


Figure 10 Typical Junction Capacitance

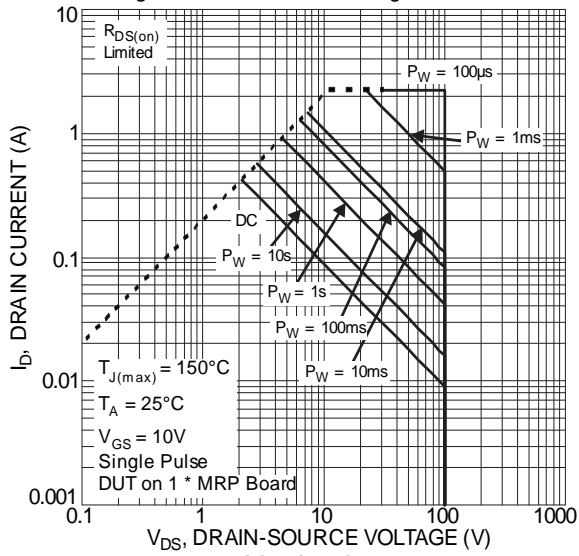
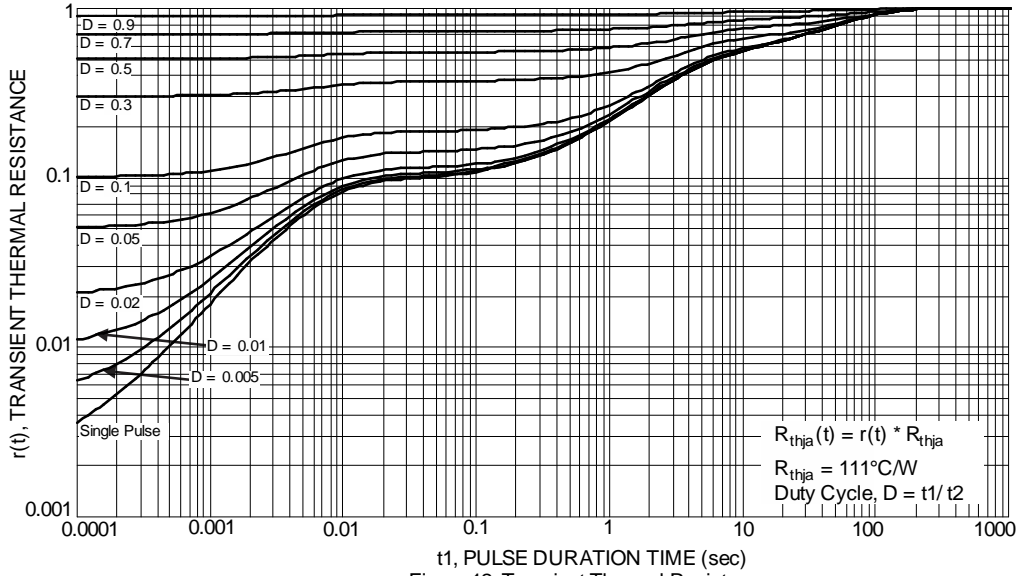


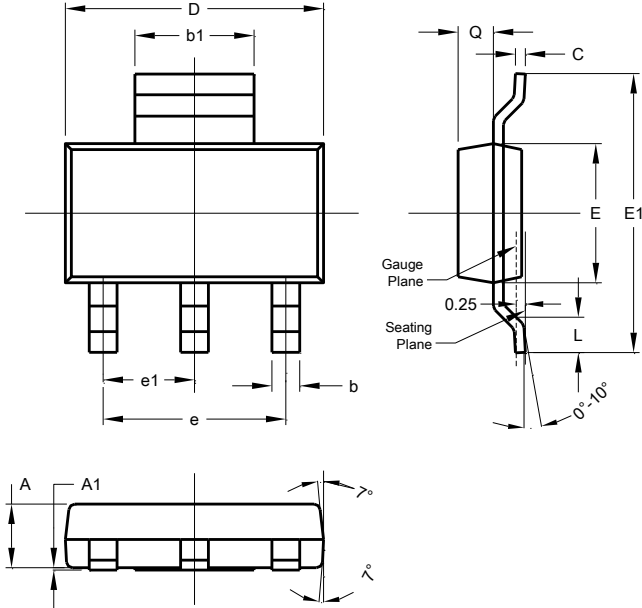
Figure 11 SOA, Safe Operation Area



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**Package Outline Dimensions**

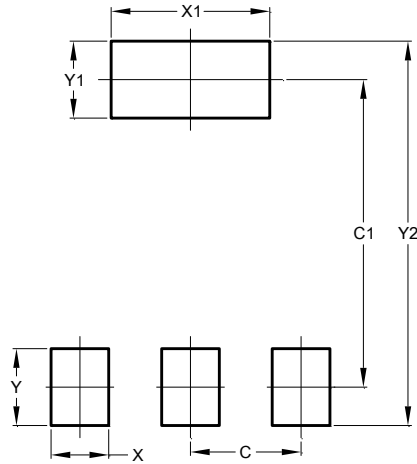
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
C2	8.00

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